/ Descriptions

Silicon PNP transistor in a TO-252 Plastic Package.

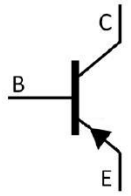
/ Features

High voltage.

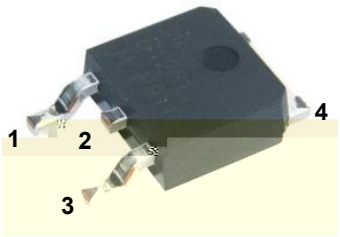
/ Applications

High voltage general purpose applications.

/ Equivalent Circuit



/ Pinning



PIN1 Base PIN 2,4 Collector PIN 3 Emitter

/ h_{FE} Classifications & Marking

See Marking Instructions.

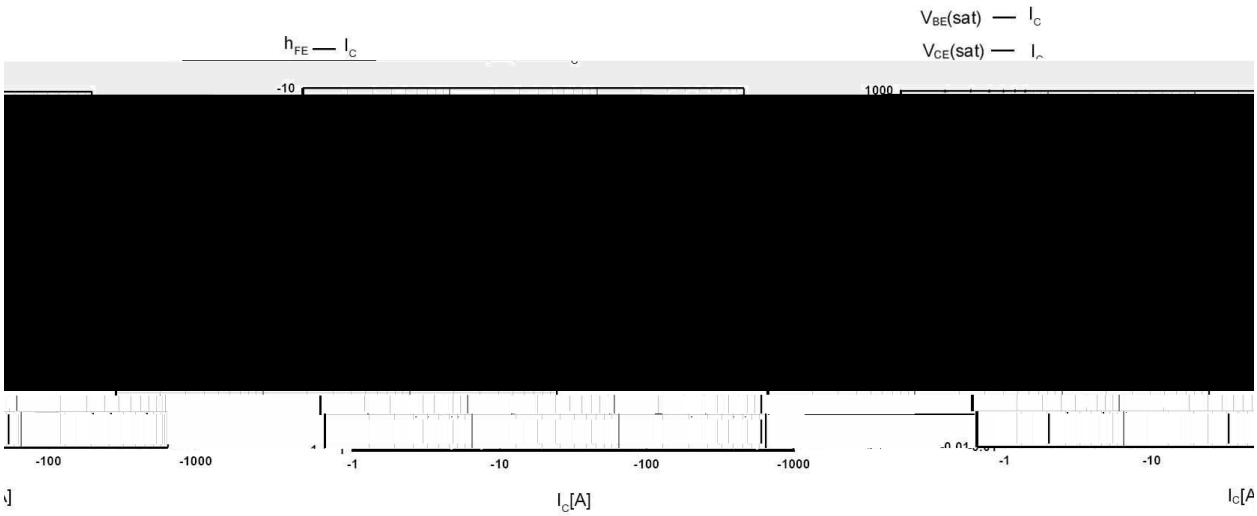
/ Absolute Maximum Ratings(Ta=25)

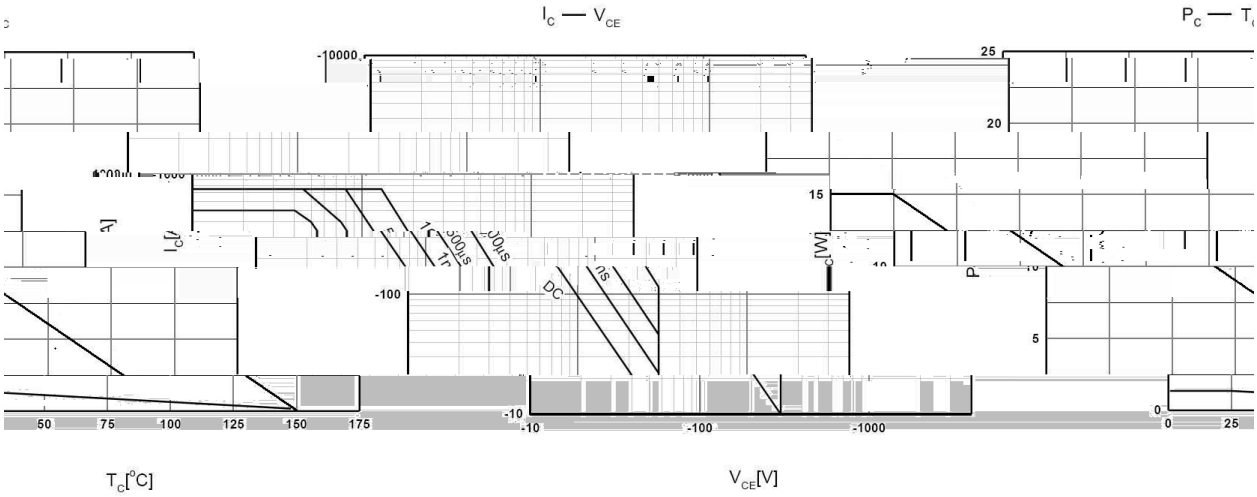
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-300	V
Collector to Emitter Voltage	V_{CEO}	-300	V
Emitter to Base Voltage	V_{EBO}	-5	V
Collector Current - Continuous	I_C	-500	mA
Collector Power Dissipation	P_C	1.56	W
Collector Power Dissipation	$P_C(T_C=25℃)$	15	W
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-55 150	℃

/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=-0.1mA I_E=0	-300			V
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=-1mA I_B=0	-300			V
Emitter to Base Breakdown Voltage	V_{EBO}	I_C=-0.1mA I_B=0	-5			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=-300V I_E=0			-100	μA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=-3V I_C=0			-100	μA
DC Current Gain	h_{FE}	V_{CE}=-10V I_C=-50mA	30		240	

/ Electrical Characteristic Curve





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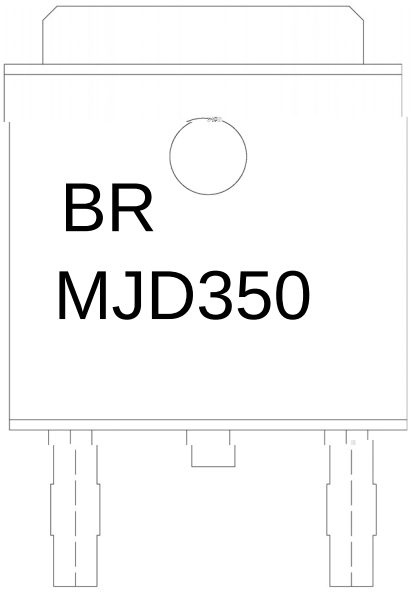
/ Marking Instructions



BR

Note:

BR:	Company Code
MJD350:	Product Type.
****:	Lot No. Code, code change with Lot No.